

East 8 USPB, USPT, WPID, JPO

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	626111	alpha or amorphous	US-PGPUB; USPAT	OR	OFF	2005/09/08 20:06
L2	602811	si or silicon	US-PGPUB; USPAT	OR	ON	2005/09/08 20:06
L3	357502	poly or polysi\$ or "polyc\$ si" or "polyc\$ silicon"	US-PGPUB; USPAT	OR	ON	2005/09/08 20:06
L4	2642878	etch\$ or patern\$ or remov\$ or planariz\$ or lap\$ or grind\$ or abrad\$ or cmp or "reduc\$ the thick\$" or "reduc\$ the thick\$"	US-PGPUB; USPAT	OR	ON	2005/09/08 20:07
L5	38377	tft or "thin film transistor"	US-PGPUB; USPAT	OR	ON	2005/09/08 20:08
L6	391710	laser	US-PGPUB; USPAT	OR	ON	2005/09/08 20:08
L7	177417	crystalliz\$	US-PGPUB; USPAT	OR	ON	2005/09/08 20:09
L8	275523	cure or cured or curing	US-PGPUB; USPAT	OR	ON	2005/09/08 19:18
L9	11075	1 with 2 with 3	US-PGPUB; USPAT	OR	ON	2005/09/08 18:22
L10	2105	7 with 2 with 3	US-PGPUB; USPAT	OR	ON	2005/09/08 18:23
L11	11535	(9 or 10)	US-PGPUB; USPAT	OR	ON	2005/09/08 18:23
L12	43996	4 with 3	US-PGPUB; USPAT	OR	ON	2005/09/08 18:23
L13	1611	11 same 12	US-PGPUB; USPAT	OR	ON	2005/09/08 18:24
L14	7032	3 with 5	US-PGPUB; USPAT	OR	ON	2005/09/08 18:24
L15	341	13 and 14	US-PGPUB; USPAT	OR	ON	2005/09/08 18:24
L16	6524	8 with 3	US-PGPUB; USPAT	OR	ON	2005/09/08 18:25
L17	758	4 same 16	US-PGPUB; USPAT	OR	ON	2005/09/08 18:25
L18	1	15 and 17	US-PGPUB; USPAT	OR	ON	2005/09/08 18:26
L19	1154	9 with laser	US-PGPUB; USPAT	OR	ON	2005/09/08 18:26
L20	1017	10 with laser	US-PGPUB; USPAT	OR	ON	2005/09/08 18:26
L21	197	15 and (19 or 20)	US-PGPUB; USPAT	OR	ON	2005/09/08 18:28

L22	80	21 and buffer	US-PGPUB; USPAT	OR	ON	2005/09/08 18:28
L23	5	8 and 22	US-PGPUB; USPAT	OR	ON	2005/09/08 18:29
L24	5	23 not 18	US-PGPUB; USPAT	OR	ON	2005/09/08 18:31
L25	182	13 same (19 or 20)	US-PGPUB; USPAT	OR	ON	2005/09/08 18:32
L26	136	25 and 14	US-PGPUB; USPAT	OR	ON	2005/09/08 18:32
L27	46	25 not 26	US-PGPUB; USPAT	OR	ON	2005/09/08 18:33
L28	136	25 not 27	US-PGPUB; USPAT	OR	ON	2005/09/08 18:34
L29	130	28 not (23 or 18)	US-PGPUB; USPAT	OR	ON	2005/09/08 18:37
L30	0	16 and 29	US-PGPUB; USPAT	OR	ON	2005/09/08 18:38
L31	5	8 and 29	US-PGPUB; USPAT	OR	ON	2005/09/08 18:41
L32	125	29 not 31	US-PGPUB; USPAT	OR	ON	2005/09/08 19:16
L33	261469	alpha or amorphous	JPO; DERWENT	OR	OFF	2005/09/08 19:16
L34	299045	poly or polysi\$ or "polyc\$ si" or "polyc\$ silicon"	JPO; DERWENT	OR	ON	2005/09/08 19:16
L35	1550644	si or silicon	JPO; DERWENT	OR	ON	2005/09/08 19:16
L36	1907698	etch\$ or patern\$ or remov\$ or planariz\$ or lap\$ or grind\$ or abrad\$ or cmp or "reduc\$ the thick\$" or "reduc\$ the thick\$"	JPO; DERWENT	OR	ON	2005/09/08 19:17
L37	39794	tft or "thin film transistor"	JPO; DERWENT	OR	ON	2005/09/08 19:17
L38	404105	laser	JPO; DERWENT	OR	ON	2005/09/08 19:18
L39	40227	crystalliz\$	JPO; DERWENT	OR	ON	2005/09/08 19:18
L40	261516	cure or cured or curing	JPO; DERWENT	OR	ON	2005/09/08 20:07
L41	3768	33 with 35 with (34 or 39)	JPO; DERWENT	OR	ON	2005/09/08 19:19
L42	18022	34 with 36	JPO; DERWENT	OR	ON	2005/09/08 19:19
L43	390	41 and 42	JPO; DERWENT	OR	ON	2005/09/08 19:20

L44	87	37 and 43	JPO; DERWENT	OR	ON	2005/09/08 19:20
L45	1785	34 with 37	JPO; DERWENT	OR	ON	2005/09/08 19:20
L46	62	44 and 45	JPO; DERWENT	OR	ON	2005/09/08 19:20
L47	20	46 and (38 or 40)	JPO; DERWENT	OR	ON	2005/09/08 19:23
L48	0	47 not 46	JPO; DERWENT	OR	ON	2005/09/08 19:21
L49	42	46 not 47	JPO; DERWENT	OR	ON	2005/09/08 19:31
L50	25	44 not 46	JPO; DERWENT	OR	ON	2005/09/08 19:42
L51	390	43 not 22	JPO; DERWENT	OR	ON	2005/09/08 19:42
L52	303	43 not 44	JPO; DERWENT	OR	ON	2005/09/08 19:43
L53	1	40 and 52	JPO; DERWENT	OR	ON	2005/09/08 19:44
L54	11	52 and (lcd or "liquid crystal" or "active matrix")	JPO; DERWENT	OR	ON	2005/09/08 19:44
L55	61	52 and transistor	JPO; DERWENT	OR	ON	2005/09/08 19:45
L56	68	54 or 55	JPO; DERWENT	OR	ON	2005/09/08 19:57
L57	235	52 not 56	JPO; DERWENT	OR	ON	2005/09/08 19:57
L58	1281949	wafer or semiconduct\$ or chip	JPO; DERWENT	OR	ON	2005/09/08 19:57
L59	176	57 and 58	JPO; DERWENT	OR	ON	2005/09/08 19:58
L60	4	59 and buffer\$	JPO; DERWENT	OR	ON	2005/09/08 19:58
L61	538275	alpha or amorphous.clm.	US-PGPUB; USPAT	OR	OFF	2005/09/08 20:08
L62	173260	(si or silicon).clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:06
L63	78291	(poly or polysi\$ or "polyc\$ si" or "polyc\$ silicon").clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:06
L64	713153	(etch\$ or patern\$ or remov\$ or planariz\$ or lap\$ or grind\$ or abrad\$ or cmp or "reduc\$ the thick\$" or "reduc\$ the thick\$").clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:07

L65	65400	(cure or cured or curing).clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:07
L66	120793	(alpha or amorphous).clm.	US-PGPUB; USPAT	OR	OFF	2005/09/08 20:08
L67	11052	(tft or "thin film transistor").clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:08
L68	97158	laser.clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:08
L69	17561	crystalliz\$.clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:09
L70	2443	66 with 62 with (63 or 69)	US-PGPUB; USPAT	OR	ON	2005/09/08 20:10
L71	7808	63 with 64	US-PGPUB; USPAT	OR	ON	2005/09/08 20:11
L72	60	67 and 70 and 71	US-PGPUB; USPAT	OR	ON	2005/09/08 20:11
L73	18	72 and buffer.clm.	US-PGPUB; USPAT	OR	ON	2005/09/08 20:11
L74	0	73 and "75"	US-PGPUB; USPAT	OR	ON	2005/09/08 20:12
L75	2	73 and 65	US-PGPUB; USPAT	OR	ON	2005/09/08 20:13
L76	16	73 not 75	US-PGPUB; USPAT	OR	ON	2005/09/08 20:13